No.3104A

2SC4218

NPN Triple Diffused Planar Silicon Transistor

Color TV Chroma Output, High-Voltage Driver Applications

Features

- High breakdown voltage
- Small reverse transfer capacitance and excellent high frequency characteristics
- Adoption of FBET process

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Peak Collector Current	i_{cp}	200	mA
Collector Dissipation	P_C	500	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55 to +150	°C

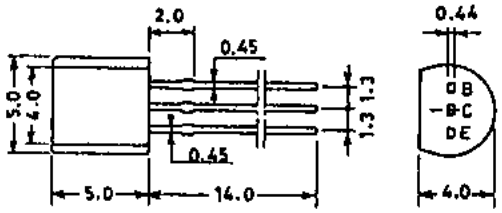
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=200V, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=1mA$	60		320	
Gain-Bandwidth Product	f_T	$V_{CE}=30V, I_C=10mA$		70		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	300			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	300			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=\infty$	5			V
Output Capacitance	c_{ob}	$V_{CB}=30V, f=1MHz$		1.5		pF
Reverse Transfer Capacitance	c_{re}	$V_{CB}=30V, f=1MHz$		1.0		pF

※ : The 2SC4218 is classified by 1mA h_{FE} as follows :

60 D 120	100 E 200	160 F 320

Case Outline 2003A
(unit : mm)

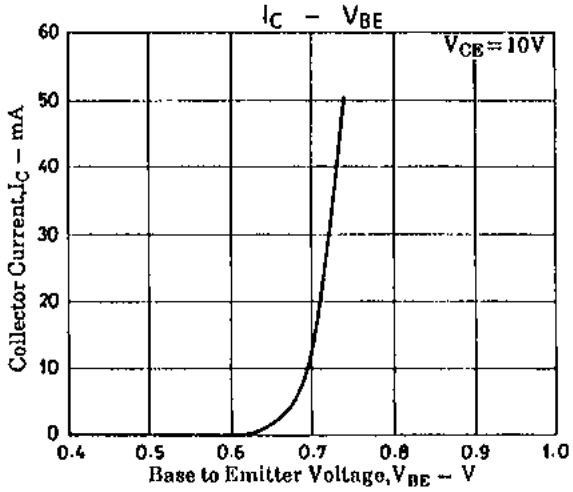


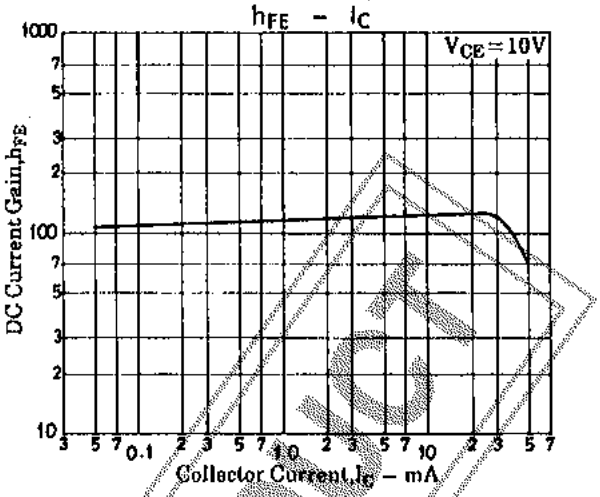
JEDEC: TO-92
EIAJ : SC-43
SANYO: NP

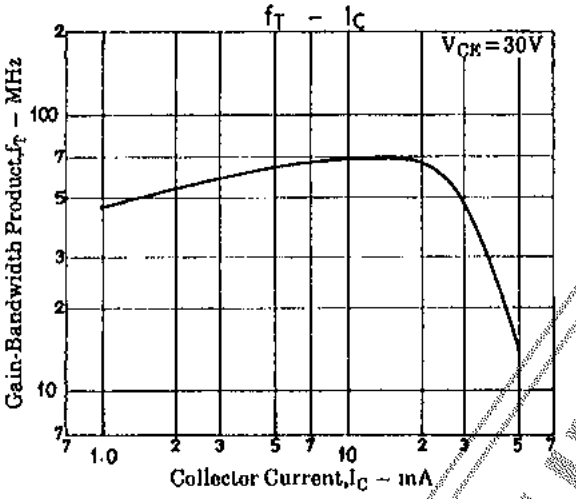
B: Base
C: Collector
E: Emitter

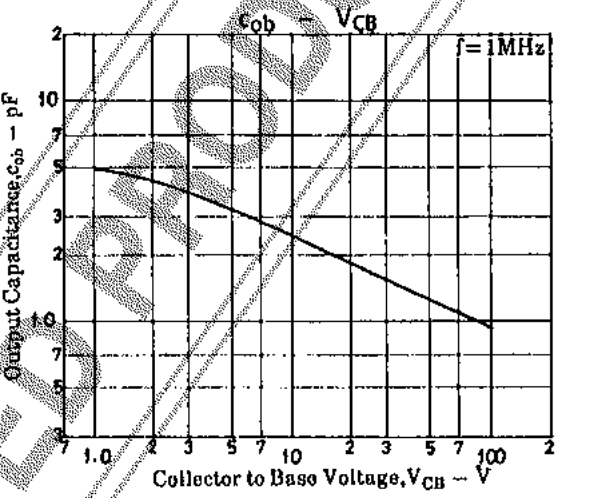
Specifications and information herein are subject to change without notice.

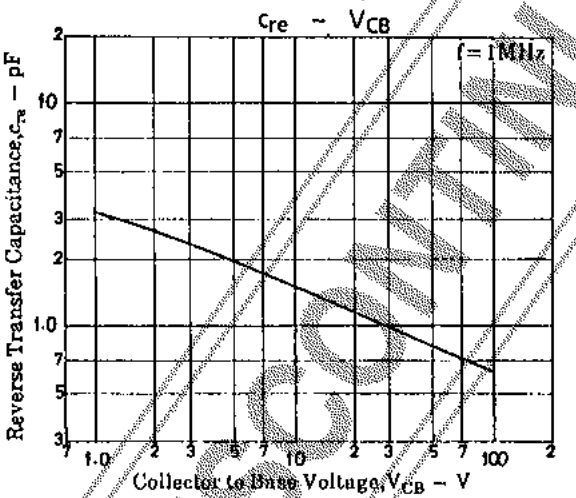
SANYO Electric Co.,Ltd. Semiconductor Overseas Marketing Div.
Natsume Bldg., 18-6, 2 chome, Yushima, Bunkyo-ku, TOKYO 113 JAPAN

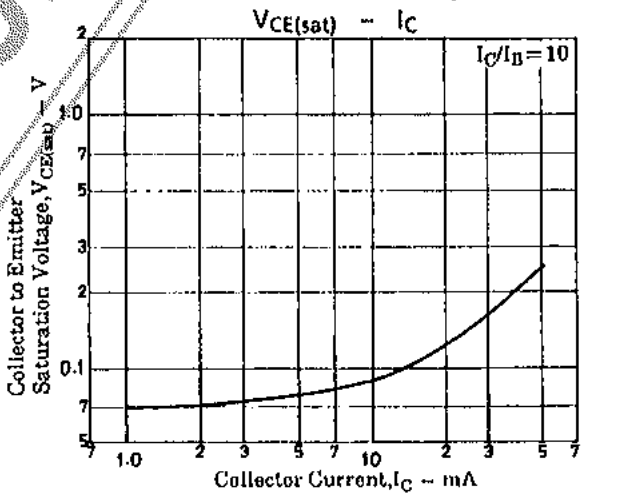


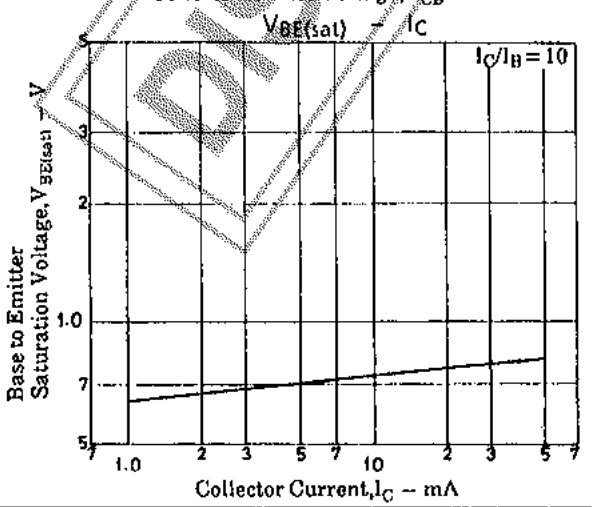


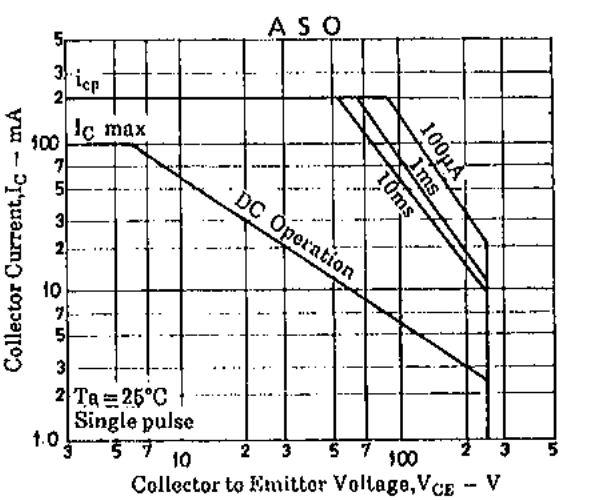


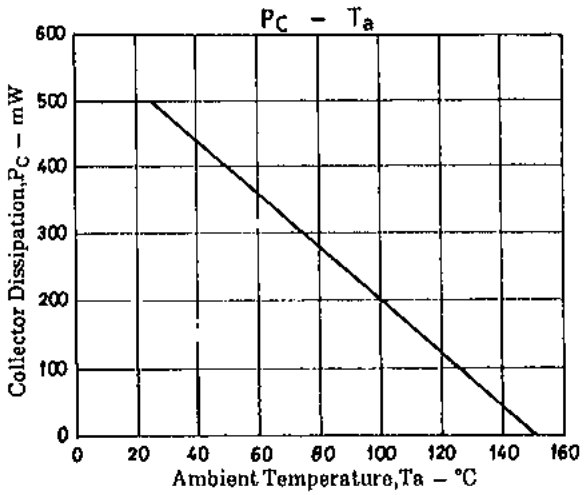












The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced.
The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use; nor for any infringements of patents or other rights of third parties which may result from its use.